

RoHS

COMPLIANT HALOGEN

FREE

Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

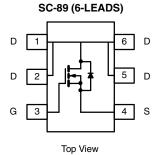
| PRODU | CT SUMMARY | | |
|---------------------|--|--------------------|-----------------------|
| V _{DS} (V) | R_{DS(on)} (Ω) | I _D (A) | Q _g (Typ.) |
| 30 | 0.099 at V _{GS} = 4.5 V | 1.2 ^a | 3.5 |
| 50 | 0.140 at V_{GS} = 2.5 V | 1.0 | 0.0 |

FEATURES

- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Load Switch for Portable Devices



Marking Code

Ordering Information: Si1070X-T1-GE3 (Lead (Pb)-free and Halogen-free)

| Parameter | | Symbol | Limit | Unit |
|--|------------------------|-----------------------------------|-----------------------|------|
| Drain-Source Voltage | | V _{DS} | 30 | v |
| Gate-Source Voltage | | V _{GS} | ± 12 | v |
| Continuous Droin Current (T 150 °C) | T _A = 25 °C | | 1.2 ^{b, c} | |
| Continuous Drain Current $(T_J = 150 \ ^{\circ}C)^a$ | T _A = 70 °C | | 1 ^{b, c} | • |
| Pulsed Drain Current | | I _{DM} | 6 | — A |
| Avalanche Current | L = 0.1 mH | I _{AS} | 9 | |
| Repetitive Avalanche Energy | L = 0.1 mH | E _{AS} | 4.01 | mJ |
| Continuous Source-Drain Diode Current | T _A = 25 °C | I _S | 0.2 ^{b, c} | А |
| | T _A = 25 °C | P- | 0.236 ^{b, c} | w |
| Maximum Power Dissipation ^a | T _A = 70 °C | P _D | 0.151 ^{b, c} | v |
| Operating Junction and Storage Temperature Ra | ange | T _J , T _{stg} | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|---|--------------|-------------------|---------|---------|------|
| Parameter | | Symbol | Typical | Maximum | Unit |
| Manimum hunsting to Americanth d | t ≤ 5 s | R _{thJA} | 440 | 530 | °C/W |
| Maximum Junction-to-Ambient ^{b, d} | Steady State | ' 'thJA | 540 | 650 | |

Notes:

a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 650 $^{\circ}\text{C/W}.$

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| Parameter | Symbol | Test Conditions | Min. | Тур. | Max. | Unit | |
|---|-------------------------|---|------|--------|-------|-------|--|
| Static | | | • | • | • | • | |
| Drain-Source Breakdown Voltage | V _{DS} | $V_{GS} = 0 V, I_D = 250 \mu A$ | 30 | | | V | |
| V _{DS} Temperature Coefficient | $\Delta V_{DS}/T_{J}$ | I _D = 250 μA | | 24.5 | | mV/°C | |
| V _{GS(th)} Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | $I_{\rm D} = 230 \ \mu \text{A}$ | | - 3.81 | | mv/°C | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$ | 0.7 | | 1.55 | V | |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 12 V$ | | | ± 100 | nA | |
| Zara Cata Valtaga Drain Current | | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | nA | |
| Zero Gate Voltage Drain Current | IDSS | $V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 85 ^{\circ}\text{C}$ | | | 10 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | V_{DS} = \geq 5 V, V_{GS} = 4.5 V | 6 | | | A | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 1.2 A | | 0.082 | 0.099 | | |
| | | V _{GS} = 2.5 V, I _D = 1.0 A | | 0.116 | 0.140 | Ω | |
| Forward Transconductance | 9 _{fs} | V _{DS} = 15 V, I _D = 1.2 A | | 5 | | S | |
| Dynamic ^b | | | • | | • | • | |
| Input Capacitance | C _{iss} | V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz | | 385 | | pF | |
| Output Capacitance | C _{oss} | | | 55 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 30 | | | |
| Tatal Oata Obarra | 0 | $V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 1.2 \text{ A}$ | | 3.8 | 8.3 | | |
| Total Gate Charge | Qg | | | 3.5 | 4.1 | | |
| Gate-Source Charge | Q _{gs} | V_{DS} = 15 V, V_{GS} = 4.5 V, I_{D} = 4.6 A | | 1.1 | | nC | |
| Gate-Drain Charge | Q _{gd} | | | 0.98 | | | |
| Gate Resistance | Rg | f = 1 MHz | | 4.7 | 6.2 | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 10 | 15 | | |
| Rise Time | t _r | V_{DD} = 15 V, R_L = 15 Ω | | 22 | 33 | ns | |
| Turn-Off DelayTime | t _{d(off)} | $\text{I}_\text{D}\cong$ 1.0 A, V_GEN = 4.5 V, R_g = 1 Ω | | 14 | 21 | | |
| Fall Time | t _f | | | 6 | 9 | | |
| Drain-Source Body Diode Characterist | ics | | | | | | |
| Pulse Diode Forward Current ^a | I _{SM} | | | | 6 | A | |
| Body Diode Voltage | V _{SD} | I _S = 1.2 A | | 0.8 | 1.2 | V | |
| Body Diode Reverse Recovery Time | t _{rr} | | | 19.4 | 29.5 | nC | |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 18.43 | 27.5 | | |
| Reverse Recovery Fall Time | ta | —— I _F = 3.8 A, dl/dt = 100 A/μs | | 16.4 | | ns | |
| Reverse Recovery Rise Time | t _b | | | 3 | | 1 | |

Notes:

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

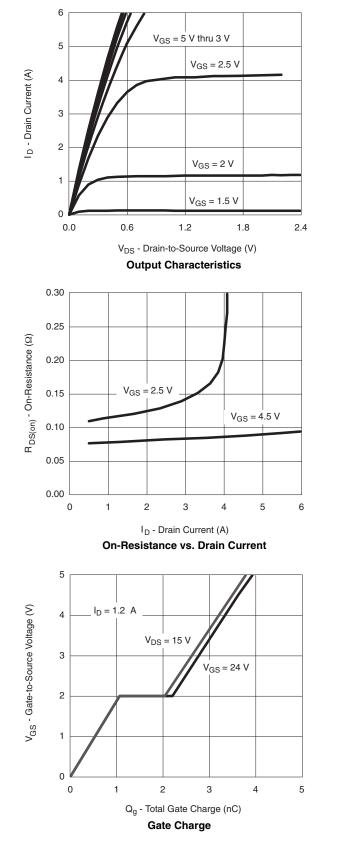
b. Guaranteed by design, not subject to production testing.

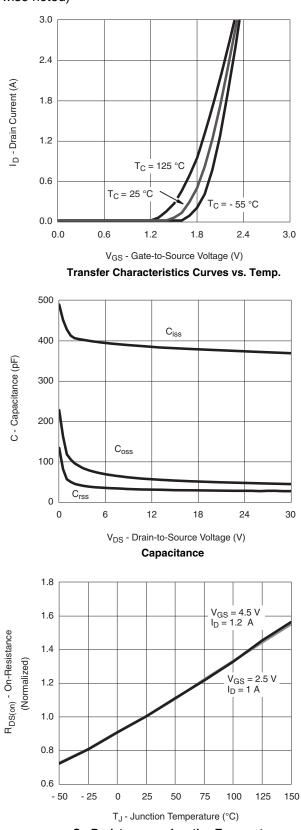
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



Si1070X Vishay Siliconix

TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





On-Resistance vs. Junction Temperature

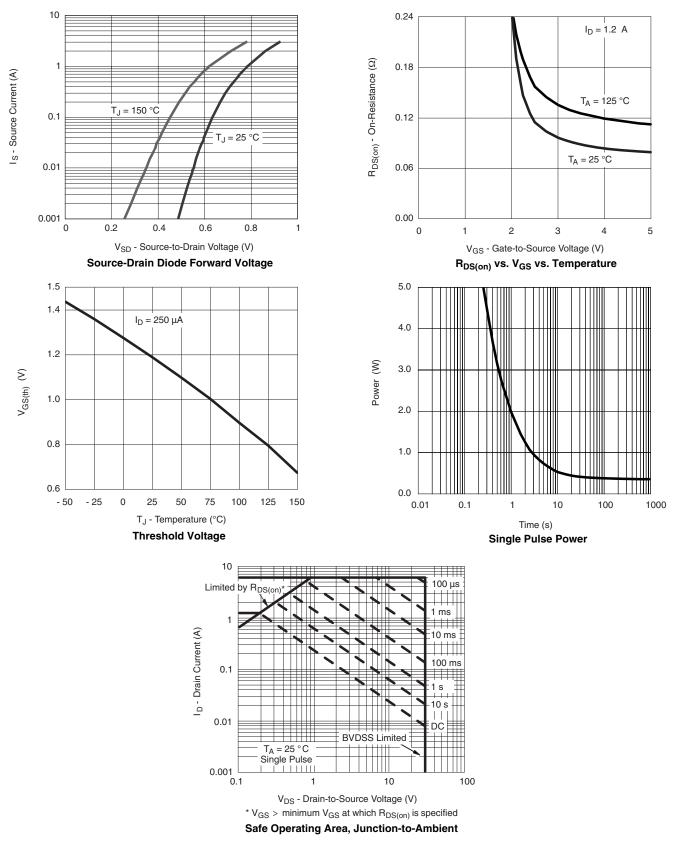
Document Number: 73893 S10-2542-Rev. D, 08-Nov-10

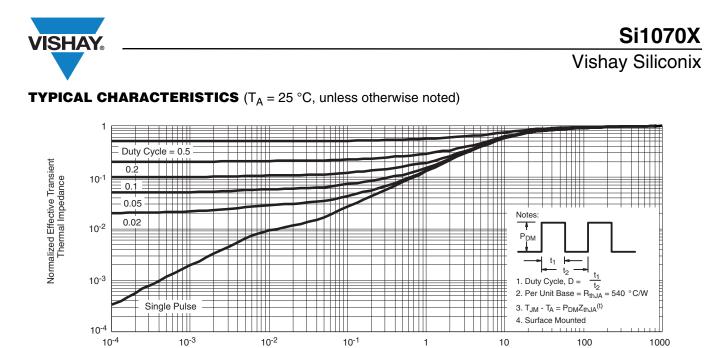
Si1070X

Vishay Siliconix



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





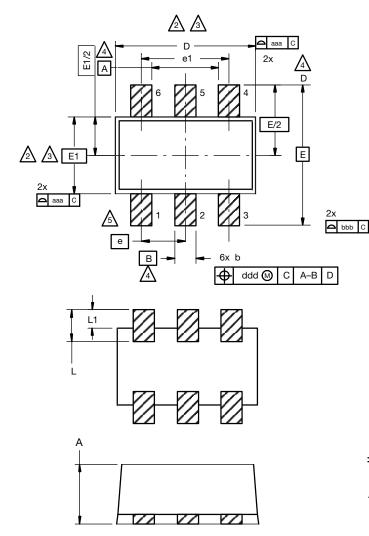
Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?73893.



Vishay Siliconix

SC-89 6-Leads (SOT-563F)



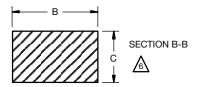
Notes

- 1. Dimensions in millimeters.
- Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.
- Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

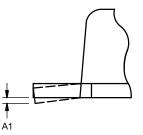
A Datums A, B and D to be determined 0.10 mm from the lead tip.

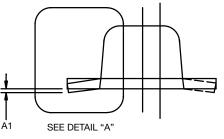
A Terminal numbers are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.









| DIM. | MILLIMETERS | | | |
|---------------------------|-----------------|------|------|--|
| | MIN. | NOM. | MAX. | |
| А | 0.56 | 0.58 | 0.60 | |
| A1 | 0 | 0.02 | 0.10 | |
| b | 0.15 | 0.22 | 0.30 | |
| С | 0.10 | 0.14 | 0.18 | |
| D | 1.50 | 1.60 | 1.70 | |
| E | 1.50 | 1.60 | 1.70 | |
| E1 | 1.15 | 1.20 | 1.25 | |
| е | 0.45 | 0.50 | 0.55 | |
| e1 | 0.95 | 1.00 | 1.05 | |
| L | 0.25 | 0.35 | 0.50 | |
| L1 | 0.10 | 0.20 | 0.30 | |
| C14-0439-Rev DWG: 5880 | /. C, 11-Aug-14 | | | |

Revision: 11-Aug-14

1 For technical questions, contact: <u>analogswitchtechsupport@vishay.com</u> Document Number: 71612

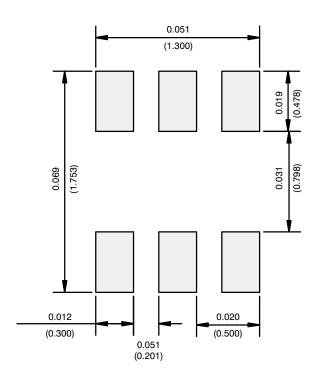
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Application Note 826

Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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